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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	B	C	P	F	S	Z
1			US 4353083 A	19821005	10	Low voltage nonvolatile memory device	257/326	257/E29.054; 257/E29.309;		Trudel, Murray L. et al.						
2			US 6418040 B1	20020709	14	Bi-directional architecture for a high-voltage flash memory device capable of preventing an over-erase	363/60	307/109; 307/110;		Meng, Anita						
3			US 20020060929 A1	20020523	16	Flash memory device capable of preventing an over-erase	365/185.29			Choi, Ki-Rwan						
4			US 20020032891 A1	20020314	51	Data processing system and data processing method	714/766			Yada, Naoki et al.						
5			US 6005809 A	19991221	14	Program and erase method for a split gate flash EEPROM	365/185.29	365/185.14; 365/185.18;		Sung, Hung-Cheng et al.						
6			US 6327187 B1	20011204	6	EPROM and flash memory cells with source-side injection	365/185.28	257/E29.128; 257/E29.309;		Bergemont, Albert et al.						
7			US 5739569 A	19980414	13	Non-volatile memory cell with oxide and nitride	257/321	257/322; 257/E29.165;		Chen, Ih-Chin						
8			US 6465306 B1	20021015	19	Simultaneous formation of charge storage and bitline	438/279	438/261; 438/264;		Ramsbey, Mark T. et al.						
9			US 6445030 B1	20020903	10	Flash memory erase speed by fluorine implant or	257/315	257/299; 257/316;		Wu, Yider et al.						
10			US 6436768 B1	20020820	15	Source drain implant during ONO formation for improved	438/266	438/257		Yang, Jean Yee-Mei et al.						
11			US 4635229 A	19870106	11	Semiconductor memory device including non-volatile	365/185.07	365/182; 365/185.25;		Okumura, Koichiro et al.						
12			US 20030067807 A1	20030410	4	Erasing method for p-channel NROM	365/185.28			Lin, Hung-Sui et al.						
13			US 20030128591 A1	20030710	16	Flash memory device and method of erasing	365/185.29	365/185.19; 365/185.27;		Mihnea, Andrei et al.						